

# Silicon-Organic Hybrid (SOH) Devices for Optical Signal Processing

C. Koos,<sup>1,2</sup> J.-M. Brosi,<sup>1</sup> P. Vorreau,<sup>1</sup> T. Vallaitis,<sup>1</sup> P. Dumon,<sup>3</sup> R. Baets,<sup>3</sup>  
B. Esembeson,<sup>4</sup> I. Biaggio,<sup>4</sup> T. Michinobu,<sup>5</sup> F. Diederich,<sup>5</sup> W. Freude<sup>1</sup> and J. Leuthold<sup>1</sup>

<sup>1</sup>Institute of High-Frequency and Quantum Electronics, University of Karlsruhe, 76131 Karlsruhe, Germany

<sup>2</sup>Now with Carl Zeiss AG, Corporate Research and Technology, 73447 Oberkochen, Germany

<sup>3</sup>Photonics Research Group, Ghent University – IMEC, B-9000 Gent, Belgium

<sup>4</sup>Department of Physics, Lehigh University, Bethlehem, PA 18015, USA

<sup>5</sup>Laboratorium für Organische Chemie, ETH Zürich, CH-8093 Zürich, Switzerland

Author e-mail: c.koos@zeiss.de; w.freude@ihq.uka.de; j.leuthold@ihq.uka.de

**Abstract:** Silicon-organic hybrid (SOH) integration allows overcoming insufficient nonlinear optical properties of silicon-on-insulator waveguides. We discuss 100 Gbit/s electro-optic modulation and demonstrate 120 Gbit/s all-optical signal processing with SOH devices.

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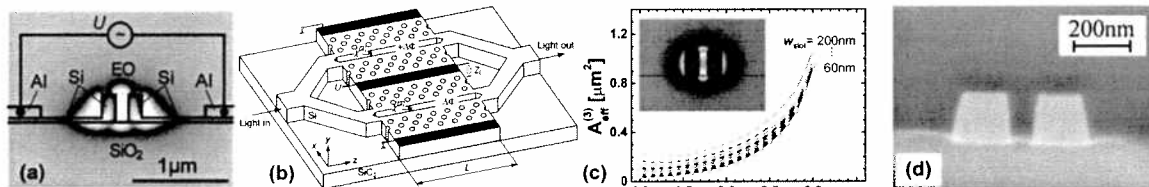
## 1. Introduction: SOH waveguides

Silicon-on-insulator (SOI) is a promising material system for dense on-chip integration of both silicon photonic and electronic devices, thereby overcoming the electronic bottleneck in short-reach high-volume data interconnects. However, certain devices are difficult to realize when relying solely on the intrinsic properties of silicon: Because of crystal symmetry, the material does not exhibit an appreciable second-order nonlinear optic effect. Silicon electro-optic modulators can therefore only be realized using free-carrier dispersion, and bandwidths of 30 GHz have been achieved in devices of 1 mm active length [1]. In addition, third-order nonlinear interaction in silicon nanophotonic waveguides is impeded by two-photon absorption and requires measures to remove free carriers [2].

These limitations can be overcome by combining SOI waveguides with dedicated low-index cladding materials [3]. In particular, organic materials offer the possibility to engineer their optical properties as desired by modifying their molecular structure. In this paper, we discuss electro-optic modulation and Kerr-type ultrafast all-optical signal processing in integrated silicon-organic hybrid (SOH) devices.

## 2. Second-order nonlinearities: Electro-optic modulators

Figure 1(a) shows a cross section of an electro-optic SOH waveguide. The waveguide core consists of two silicon strips on a SiO<sub>2</sub> buffer layer and is covered by a low-index electro-optic cladding material (EO). Field discontinuities at the core-cladding interfaces provide strong interaction of the guided mode with the electro-optic material, see field plot in Fig. 1(a). Both Si strips and the adjacent thin slabs are doped and connected to aluminum electrodes. A voltage applied to the electrodes induces a large electric field in the narrow gap between the strips. The design shows potential for efficient electro-optic modulation at more than 100 GHz in 1.2 mm long devices [4]. The conductive Si slabs can be replaced by photonic crystal (PhC) structures. Fig. 1(b) shows a schematic of an SOH-PhC-based Mach-Zehnder modulator. By appropriate design, the optical group velocity in the PhC-sections can be reduced to 4% of the vacuum speed of light with flat dispersion over an optical bandwidth of 1 THz. For 1V modulation amplitude, a bandwidth of 78 GHz is predicted for 80 μm long PhC sections, allowing for 100 Gbit/s transmission [5].



**Fig. 1** (a) Cross section of an SOH waveguide for electro-optic phase modulation. (b) PhC-based SOH Mach-Zehnder modulator. (c) Effective area as a function of the linear refractive index  $n$  of the nonlinear cover material. Strip width  $w$  and waveguide height  $h$  optimized for fixed slot widths  $w_{\text{slot}}$ . Inset: Field plot of the horizontal E-field component. (d) Cross section of fabricated slot waveguide functionalized with organic film.

## 3. Third-order nonlinearities: All-optical signal processing

For all-optical signal processing, the optical mode has to be confined to a small effective area within the nonlinear cover material. This can be achieved by using slot waveguides [6]. By optimizing the waveguide dimensions, effective cross sections smaller than  $0.1 \mu\text{m}^2$  can be obtained, see Fig. 1(c) [7]. We functionalized SOI strip waveguides by molecular beam deposition of an amorphous organic film of DDMEBT (derivative 2 in [9], nonlinear index  $n_2 \approx 2 \times 10^{-17} \text{m}^2/\text{W}$ ). These waveguides exhibit nonlinearities of  $\gamma = 10^5 \text{W}^{-1}\text{km}^{-1}$  at  $\lambda = 1.55 \mu\text{m}$  and were used in a proof-of-principle experiment to demonstrate all-optical demultiplexing of a 120 Gbit/s data stream to 10 Gbit/s [8].

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